光鋐科技股份有限公司

Epileds Technologies, Inc.

Product specification of 42 x42 *mil* IR *LED chip*

1. Scope:

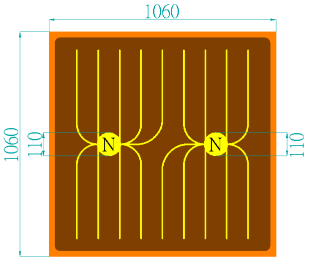
   This specification applies to AlGaAs metal bonding 42 x 42mil IR LED chip, BN-D4242J-A3。

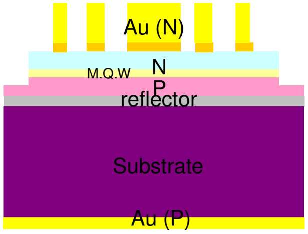
2. Materials：

   2.1 P-pad：Au alloy。
   2.2 N-pad：Au alloy。

3. Dimensions：

   3.1 Chip size：1060±25μm x 1060±25μm。
   3.2 N-pad：φ110±10μm。
   3.3 Chip thickness：200μm±25μm。





4. Electro-optical characteristics and specification: (Tc=25°C)

4.1 Electro-optical characteristics

Test parameter	Condition	Min	Typ	Max	Unit
Peak wavelength(Wp)	700mA	800	-	900	nm
Forward voltage(Vf1)	700mA	1.4	-	2.4	V
Forward voltage(Vf4)	10uA	0.7	-	-	V
Reverse current (Ir)	-10V	0	-	2	uA
Iv@845nm-855nm	700mA	85	-	90	mW/sr
		90	-	100	
		100	-	110	

4.2 Absolute Maximum Ratings

Parameter	Symbol	Condition	Rating	Unit
Forward DC Current	If	Ta=25℃	≦1000	mA
Reverse Voltage	Vr	Ta=25℃	≦10	V
Junction Temperature	Tj	-	≦115	℃
Operating ambient temperature	Ta	Chip	-40~+85	℃
Storage Temperature	Tstg	Chip-on-tape/storage	5~35	℃
		Chip-on-tape/transportation	-20~+65	℃
Temperature during Packaging	-	-	280(＜10sec)	℃

Notes:Maximum ratings are package dependent. The above maximum rating were determined using a metal core printed circuit board(MCPCB) without an encapsulant. Stresses in encess of the absolute maximum rating such as forward and junction temperature may cause damage to the led.

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** The detail technical and reliability datasheet are also available for your reference, please be free to contact us.*